Gb Stringfellow

List of Publications by Year
in descending order

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110 papers	4,981 citations	100601 38 h-index	107981 68 g-index
111 all docs	111 docs citations	111 times ranked	1878 citing authors

#	Article	IF	Citations
1	Epitaxial growth of metastable semiconductor alloys. Journal of Crystal Growth, 2021, 564, 126065.	0.7	5
2	Thermodynamic considerations for epitaxial growth of III/V alloys. Journal of Crystal Growth, 2017, 468, 11-16.	0.7	13
3	Enhanced cation-substituted p-type doping in GaP from dual surfactant effects. Journal of Crystal Growth, 2010, 312, 174-179.	0.7	16
4	Microstructures produced during the epitaxial growth of InGaN alloys. Journal of Crystal Growth, 2010, 312, 735-749.	0.7	142
5	Effects of dimethylhydrazine on Zn, C, and H doping of GaP. Journal of Crystal Growth, 2008, 310, 2702-2706.	0.7	1
6	Zn enhancement during surfactant-mediated growth of GaInP and GaP. Journal of Crystal Growth, 2006, 287, 647-651.	0.7	14
7	Thermodynamics of modern epitaxial growth processes. , 2004, , 1-26.		1
8	Sb and Bi surfactant effects on homo-epitaxy of GaAs on () patterned substrates. Journal of Crystal Growth, 2004, 265, 367-374.	0.7	41
9	Development and current status of organometallic vapor phase epitaxy. Journal of Crystal Growth, 2004, 264, 620-630.	0.7	15
10	Te surfactant effects on the morphology of patterned (001) GaAs homoepitaxy. Journal of Crystal Growth, 2004, 269, 276-283.	0.7	21
11	Effects of Surfactants N and Br on Ordering in GaInP. Materials Research Society Symposia Proceedings, 2003, 794, 43.	0.1	1
12	Time dependent surfactant effects on growth of GaInP heterostructures by organometallic vapor phase epitaxy. Journal of Crystal Growth, 2002, 234, 327-336.	0.7	8
13	Isoelectronic surfactant-induced surface step structure and correlation with ordering in GaInP. Journal of Crystal Growth, 2002, 235, 15-24.	0.7	22
14	Fundamental aspects of organometallic vapor phase epitaxy. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2001, 87, 97-116.	1.7	34
15	Enhancement of compositional modulation in GaInP epilayers by the addition of surfactants during organometallic vapor phase epitaxy growth. Journal of Crystal Growth, 2001, 233, 490-502.	0.7	17
16	Surface processes in OMVPE â€“ the frontiers. Journal of Crystal Growth, 2000, 221, 1-11.	0.7	40
17	Isoelectronic dopant induced ordering transition in GaInP grown by organometallic vapour phase epitaxy. Surface Science, 2000, 457, L381-L385.	0.8	6
18	Pyrolysis of monomethylhydrazine for organometallic vapor-phase epitaxy (OMVPE) growth. Journal of Crystal Growth, 1999, 204, 247-255.	0.7	13

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19	Effect of P precursor on surface structure and ordering in GaInP. Journal of Crystal Growth, 1998, 193, 1-8.	0.7	16
20	Pyrolysis of tertiarybutylamine alone and with trimethylgallium for GaN growth. Journal of Crystal Growth, 1998, 191, 1-7.	0.7	15
21	Effect of Te doping on step structure and ordering in GaInP. Journal of Crystal Growth, 1998, 195, 13-20.	0.7	25
22	Order and Surface Processes in III-V Semiconductor Alloys. MRS Bulletin, 1997, 22, 27-32.	1.7	33
23	Chapter 1 Materials Issues in High-Brightness Light-Emitting Diodes. Semiconductors and Semimetals, 1997, , 1-45.	0.4	20
24	Effects of growth temperature and ratio on surface structure and ordering in Ga0.5In0.5P. Journal of Crystal Growth, 1997, 170, 219-224.	0.7	24
25	Chemical beam epitaxy of InP without precracking using tertiarybutylbis(dimethylamino)phosphine. Journal of Crystal Growth, 1997, 172, 1-4.	0.7	4
26	Use of ratio to produce heterostructures in ordered GaInP. Journal of Crystal Growth, 1997, 170, 263-269.	0.7	12
27	Effect of growth parameters on step structure and ordering in GaInP. Journal of Crystal Growth, 1997, 174, 585-592.	0.7	13
28	Solubility of nitrogen in binary Illâ€“V systems. Journal of Crystal Growth, 1997, 178, 1-7.	0.7	132
29	OMVPE growth of metastable GaAsSb and GaInAsSb alloys using TBAs and TBDMSb. Journal of Crystal Growth, 1997, 179, 1-9.	0.7	22
30	A comparison of the reactions of phosphorus precursors on deposited GaP and InP films. Journal of Crystal Growth, 1997, 181, 321-325.	0.7	11
31	Lattice-Matched InAsN(X=0.38) on GaAs Grown by Molecular Beam Epitaxy. Materials Research Society Symposia Proceedings, 1996, 423, 335.	0.1	21
32	Incomplete Solubility in Nitride Alloys. Materials Research Society Symposia Proceedings, 1996, 449, 871.	0.1	42
33	Tris-dimethylaminophosphorus reactions at low pressure on GaP, InP and quartz surfaces. Journal of Crystal Growth, 1996, 162, 1-6.	0.7	11
34	Step structure during OMVPE growth of ordered GaInP. Journal of Crystal Growth, 1996, 163, 128-134.	0.7	16
35	CBE growth of InP using BPE and TBP: a comparative study. Journal of Crystal Growth, 1996, 164, 104-111.	0.7	5
36	Compositional Ordering in GaInP for Heterostructure Formation. Materials Research Society Symposia Proceedings, 1995, 417, 207.	0.1	2

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37	Ordering in GaInP grown at low temperatures. Journal of Crystal Growth, 1995, 146, 558-563.	0.7	34
38	Growth of GaSb using trisdimethylaminoantimony. Journal of Crystal Growth, 1995, 151, 1-8.	0.7	24
39	OMVPE growth of InAsSb using novel precursors. Journal of Crystal Growth, 1995, 156, 311-319.	0.7	15
40	InTlSb growth by OMVPE. Journal of Crystal Growth, 1995, 156, 320-326.	0.7	30
41	Trisdimethylaminoantimony: a new Sb source for low temperature epitaxial growth of InSb. Journal of Crystal Growth, 1994, 143, 15-21.	0.7	29
42	Order/disorder heterostructure in Ga0.5In0.5P with Î”Eg = 160 meV. Journal of Crystal Growth, 1994, 145, 140-146.	0.7	65
43	Characterization of ordered and disordered Ga0.51In0.49P domains by micro Raman spectroscopy. Journal of Crystal Growth, 1994, 145, 171-178.	0.7	6
44	Fundamentals of thin film growth. Journal of Crystal Growth, 1994, 137, 212-223.	0.7	8
45	Effect of Substrate Misonrentation on Ordering in Ga0.5In0.5P. Materials Research Society Symposia Proceedings, 1994, 340, 123.	0.1	3
46	Chemical Beam Epitaxial Growth of GaP and InP Using Alternative, Safer Precursors. Materials Research Society Symposia Proceedings, 1994, 340, 167.	0.1	4
47	InAsBi alloys grown by organometallic vapor phase epitaxy. Journal of Crystal Growth, 1993, 134, 29-34.	0.7	68
48	Triisopropylindium: decomposition study and use for low temperature growth of InAs. Journal of Crystal Growth, 1993, 126, 309-316.	0.7	6
49	Diisopropylantimonyhydride (DIPSbH) for low temperature epitaxial growth of InSb. Journal of Crystal Growth, 1993, 132, 371-376.	0.7	19
50	Novel precursors for organometallic vapor phase epitaxy. Journal of Crystal Growth, 1993, 128, 503-510.	0.7	25
51	Compositional Ordering in Semiconductor Alloys. Materials Research Society Symposia Proceedings, 1993, 312, 35.	0.1	8
52	Triisopropylindium for OMVPE growth. Journal of Crystal Growth, 1992, 124, 88-92.	0.7	9
53	Tertiarybutyldimethylantimony for InSb growth. Journal of Crystal Growth, 1992, 124, 142-149.	0.7	21
54	Organometallic vapor-phase epitaxial growth of AlxGa1â^'xSb and AlxGa1â^'xAsySb1â^'y. Journal of Crystal Growth, 1991, 113, 441-448.	0.7	29

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55	GaInP/AlGaInP strained quantum wells grown using atmospheric pressure organometallic vapor phase epitaxy. Journal of Crystal Growth, 1991, 109, 285-291.	0.7	23
56	Radical reactions in pyrolysis of triethylarsine and diethylarsine. Journal of Crystal Growth, 1991, 112, 515-524.	0.7	2
57	OMVPE growth and characterization of Bi-containing IIIâ€“V alloys. Journal of Crystal Growth, 1991, 107, 416-421.	0.7	23
58	Fundamental aspects of vapor growth and epitaxy. Journal of Crystal Growth, 1991, 115, 1-11.	0.7	35
59	Effect of growth rate on properties of Ga 0.51 In 0.49 P grown by organometallic vapor phase epitaxy. Journal of Crystal Growth, 1991, 109, 279-284.	0.7	55
60	Comparative pyrolysis studies of ethylarsines. Journal of Crystal Growth, 1991, 107, 32-36.	0.7	10
61	Organometallic vapor phase epitaxial growth of a new quarternary semiconductor alloy Ga1â^'xInxP1â^'ySby. Journal of Crystal Growth, 1990, 106, 208-216.	0.7	13
62	Alternate sources and growth chemistry for OMVPE and CBE processes. Journal of Crystal Growth, 1990, 105, 260-270.	0.7	34
63	Decomposition mechanisms of trimethylgallium. Journal of Crystal Growth, 1990, 102, 103-116.	0.7	94
64	Decomposition mechanisms of trimethylarsine. Journal of Crystal Growth, 1990, 102, 117-125.	0.7	22
65	Kinetics of the reaction between trimethylgallium and arsine. Journal of Crystal Growth, 1990, 102, 126-136.	0.7	60
66	Mechanisms of GaAs growth using tertiarybutylarsine and trimethylgallium. Journal of Crystal Growth, 1989, 94, 673-682.	0.7	24
67	Reaction mechanisms in OMVPE growth of GaAs determined using D2 labelling experiments. Progress in Crystal Growth and Characterization, 1989, 19, 115-123.	0.8	6
68	OMVPE growth of GaAs using dimethylarsine. Journal of Crystal Growth, 1989, 96, 497-504.	0.7	14
69	Decomposition mechanisms of tertiarybutylarsine. Journal of Crystal Growth, 1989, 94, 663-672.	0.7	95
70	The effect of supplemental t-butyl radicals on the pyrolysis of tertiarybutylarsine, tertiarybutylphosphine, and ditertiarybutylarsine. Journal of Crystal Growth, 1989, 98, 309-316.	0.7	30
71	Ordered structures and metastable alloys grown by OMVPE. Journal of Crystal Growth, 1989, 98, 108-117.	0.7	55
72	Organometallic vapor phase epitaxial growth studies of GaP1â^'xSbx and InP1â^'xSbx. Journal of Crystal Growth, 1989, 98, 679-689.	0.7	23

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73	OMVPE growth mechanism for GaP using tertiarybutylphosphine and trimethylgallium. Journal of Crystal Growth, 1989, 96, 906-914.	0.7	34
74	Non-Hydride Group V Sources for Omvpe. Materials Research Society Symposia Proceedings, 1989, 145, 171.	0.1	3
75	Ordering in III/V Alloys. Materials Research Society Symposia Proceedings, 1989, 163, 893.	0.1	0
76	OMVPE growth of the new semiconductor alloys GaP1â^'xSbx and InP1â^'xSbx. Journal of Crystal Growth, 1988, 93, 62-69.	0.7	43
77	Mass spectrometric studies of trimethylindium pyrolysis. Journal of Crystal Growth, 1988, 92, 591-604.	0.7	102
78	A mass spectrometric study of the simultaneous reaction mechanism of TMIn and PH3 to grow InP. Journal of Crystal Growth, 1988, 92, 605-615.	0.7	41
79	GaAs growth using tertiarybutylarsine and trimethylgallium. Journal of Crystal Growth, 1988, 93, 15-19.	0.7	58
80	Mass spectrometric studies of phosphine pyrolysis and OMVPE growth of InP. Journal of Crystal Growth, 1987, 85, 148-153.	0.7	82
81	The kinetic aspects of ordering in GaAs1-xSbx grown by organometallic vapor phase epitaxy. Journal of Crystal Growth, 1987, 85, 175-181.	0.7	82
82	Decomposition kinetics of OMVPE precursors. Journal of Crystal Growth, 1986, 75, 247-254.	0.7	86
83	Doping studies for InP grown by organometallic vapor phase epitaxy. Journal of Crystal Growth, 1986, 74, 535-542.	0.7	48
84	The role of impurities in III/V semiconductors grown by organometallic vapor phase epitaxy. Journal of Crystal Growth, 1986, 75, 91-100.	0.7	85
85	MOVPE growth of InP using isobutylphosphine and tert-butylphosphine. Journal of Crystal Growth, 1986, 77, 11-18.	0.7	91
86	High quality GaxIn1â^'xP (x = 0.65, 0.69) grown by OMVPE. Journal of Crystal Growth, 1986, 78, 63-68.	0.7	12
87	Chapter 3 Organometallic Vapor-Phase Epitaxial Growth of IIIâ€“V Semiconductors. Semiconductors and Semimetals, 1985, , 209-259.	0.4	20
88	Thermodynamic aspects of OMVPE. Journal of Crystal Growth, 1984, 70, 133-139.	0.7	72
89	A critical appraisal of growth mechanisms in MOVPE. Journal of Crystal Growth, 1984, 68, 111-122.	0.7	169
90	AlxGa1â^'xAsySb1â^'y phase diagram. Journal of Crystal Growth, 1983, 62, 1-6.	0.7	84

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91	Immiscibility and spinodal decomposition in III/V alloys. Journal of Crystal Growth, 1983, 65, 454-462.	0.7	90
92	OMVPE growth of GaAs1-xSbx: solid composition. Journal of Crystal Growth, 1983, 64, 413-415.	0.7	82
93	Reply to comment on â€œmiscibility gaps in quaternary III/V alloysâ€•by B. De Cremoux, P. Hirtz and J. Ricciardi. Journal of Crystal Growth, 1983, 61, 179.	0.7	0
94	Thermodynamic aspects of organometallic vapor phase epitaxy. Journal of Crystal Growth, 1983, 62, 225-229.	0.7	135
95	OMVPE growth of GaInAs. Journal of Crystal Growth, 1983, 64, 461-470.	0.7	75
96	OMVPE growth of GaInP. Journal of Crystal Growth, 1983, 62, 648-650.	0.7	36
97	OMVPE growth of InP using TMIn. Journal of Crystal Growth, 1983, 63, 8-12.	0.7	72
98	Miscibility gaps in quaternary III/V alloys. Journal of Crystal Growth, 1982, 58, 194-202.	0.7	328
99	OMVPE growth of AlxGa1â^'xAs. Journal of Crystal Growth, 1981, 55, 42-52.	0.7	78
100	Vapor Phase Growth. , 1980, , 181-220.		2
101	VPE growth of AlxGa1â^'xAs. Journal of Crystal Growth, 1978, 43, 47-60.	0.7	57
102	Calculation of distribution coefficients of donors in III-V semiconductors. Journal of Physics and Chemistry of Solids, 1974, 35, 775-783.	1.9	24
103	Calculation of ternary and quaternary IIIâ€“V phase diagrams. Journal of Crystal Growth, 1974, 27, 21-34.	0.7	249
104	Calculation of regular solution interaction parameters in semiconductor solid solutions. Journal of Physics and Chemistry of Solids, 1973, 34, 1749-1751.	1.9	102
105	The importance of lattice mismatch in the growth of GaxIn1â^'xP epitaxial crystals. Journal of Applied Physics, 1972, 43, 3455-3460.	1.1	310
106	Calculation of ternary phase diagrams of IIIâ€“V systems. Journal of Physics and Chemistry of Solids, 1972, 33, 665-677.	1.9	178
107	The calculation of regular solution interaction parameters between elements from groups III, IV and V of the periodic table. Materials Research Bulletin, 1971, 6, 371-379.	2.7	48
108	Calculation of iiiâ€“v ternary phase diagrams: In-Ga-As and In-As-Sb. Journal of Physics and Chemistry of Solids, 1969, 30, 1779-1791.	1.9	146

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109	Use of the Newly-Developed Triisopropylindium for Omvpe Growth of Inas. , 0, , .		0
110	Adsorption and desorption of the surfactant Sb on GaInP grown by organometallic vapor phase epitaxy. , 0, , .		0